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# FQA36P15

# P-Channel QFET<sup>®</sup> MOSFET -150 V, -36 A, 90 mΩ

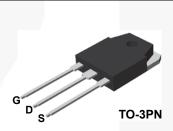
#### Features

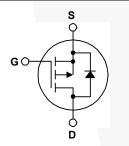
- -36 A, -150 V,  $R_{DS(on)}$  = 90 m $\Omega$  (Max) @V<sub>GS</sub> = -10 V, I<sub>D</sub> = -18 A This P-Channel enhancement mode power MOSFET is
- Low Gate Charge (Typ. 81 nC)
- Low Crss (Typ. 110 pF)
- 100% Avalanche Tested
- 175°C Maximum Junction Temperature Rating

FQA36P15 — P-Channel QFET<sup>®</sup> MOSFET

#### Description

This P-Channel enhancement mode power MOSFET is produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, audio amplifier, DC motor control, and variable switching power applications.





#### Absolute Maximum Ratings T<sub>C</sub> = 25°C unless otherwise noted.

Symbol	Parameter           Drain-Source Voltage		FQA36P15	Unit	
V <sub>DSS</sub>			-150	V	
I <sub>D</sub>	Drain Current - Continuous ( $T_C = 25^{\circ}C$ )		-36	А	
	- Continuous (T <sub>C</sub> = 100°C)		-25.5	А	
I <sub>DM</sub>	Drain Current - Pulsed	(Note 1)	-144	А	
V <sub>GSS</sub>	Gate-Source Voltage		± 30	V	
E <sub>AS</sub>	Single Pulsed Avalanche Energy	(Note 2)	1400	mJ	
I <sub>AR</sub>	Avalanche Current	(Note 1)	-36	А	
E <sub>AR</sub>	Repetitive Avalanche Energy	(Note 1)	29.4	mJ	
dv/dt	Peak Diode Recovery dv/dt	(Note 3)	-5.0	V/ns	
P <sub>D</sub>	Power Dissipation (T <sub>C</sub> = 25°C)		294	W	
	- Derate above 25°C		1.96	W/°C	
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Temperature Range		-55 to +175	°C	
TL	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds		300	°C	

#### **Thermal Characteristics**

Symbol	Parameter	FQA36P15	Unit	
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case, Max.	0.51	°C/W	
$R_{ ext{ heta}CS}$	Thermal Resistance, Case-to-Sink, Typ.	0.24	°C/W	
$R_{\thetaJA}$	Thermal Resistance, Junction-to-Ambient, Max.	40	°C/W	

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## Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FQA36P15	FQA36P15	TO-3PN	Tube	N/A	N/A	30 units

### Electrical Characteristics T<sub>C</sub> = 25°C unless otherwise noted.

Symbol	Parameter	Test Conditions	Min	Тур	Max	Unit
Off Charac	teristics					
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	$V_{GS}$ = 0 V, I <sub>D</sub> = -250 µA	-150			V
$\Delta BV_{DSS}/\Delta T_J$	Breakdown Voltage Temperature Coefficient	$I_D = -250 \ \mu A$ , Referenced to $25^{\circ}C$		-0.13		V/°C
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	$V_{DS}$ = -150 V, $V_{GS}$ = 0 V			-10	μA
		$V_{DS}$ = -120 V, $T_{C}$ = 150°C			-100	μA
I <sub>GSSF</sub>	Gate-Body Leakage Current, Forward	$V_{GS}$ = -25 V, $V_{DS}$ = 0 V			-100	nA
I <sub>GSSR</sub>	Gate-Body Leakage Current, Reverse	$V_{GS}$ = 25 V, $V_{DS}$ = 0 V			100	nA
On Charact	eristics					
V <sub>GS(th)</sub>	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = -250 \ \mu A$	-2.0		-4.0	V
R <sub>DS(on)</sub>	Static Drain-Source On-Resistance	V <sub>GS</sub> = -10 V, I <sub>D</sub> = -18 A		0.076	0.09	Ω
9 <sub>FS</sub>	Forward Transconductance	$V_{DS}$ = -40 V, I <sub>D</sub> = -18 A		19.5		S
Dynamic Ch	haracteristics					
C <sub>iss</sub>	Input Capacitance	$V_{DS}$ = -25 V, $V_{GS}$ = 0 V,		2550	3320	pF
C <sub>oss</sub>	Output Capacitance	f = 1.0 MHz		710	920	pF
C <sub>rss</sub>	Reverse Transfer Capacitance			110	140	pF
Switching C	Characteristics					
t <sub>d(on)</sub>	Turn-On Delay Time	$V_{DD} = -75 \text{ V}, \text{ I}_{D} = -36 \text{ A},$		50	110	ns
t <sub>r</sub>	Turn-On Rise Time	- R <sub>G</sub> = 25 Ω 		350	710	ns
t <sub>d(off)</sub>	Turn-Off Delay Time			155	320	ns
t <sub>f</sub>	Turn-Off Fall Time			150	310	ns
Qg	Total Gate Charge	V <sub>DS</sub> = -120 V, I <sub>D</sub> = -36 A,		81	105	nC
Q <sub>gs</sub>	Gate-Source Charge	V <sub>GS</sub> = -10 V	-	19		nC
Q <sub>gd</sub>	Gate-Drain Charge	(Note 4)		42		nC
Drain-Sourc	ce Diode Characteristics and Maximum Ratings	3	-			
I <sub>S</sub>	Maximum Continuous Drain-Source Diode Forward Current				-36	Α
I <sub>SM</sub>	Maximum Pulsed Drain-Source Diode Forward Current				-144	Α
V <sub>SD</sub>	Drain-Source Diode Forward Voltage	V <sub>GS</sub> = 0 V, I <sub>S</sub> = -36 A			-4.0	V
t <sub>rr</sub>	Reverse Recovery Time	V <sub>GS</sub> = 0 V, I <sub>S</sub> = -36 A,		198		ns
Q <sub>rr</sub>	Reverse Recovery Charge	dI <sub>F</sub> / dt = 100 A/μs		1.45		μC

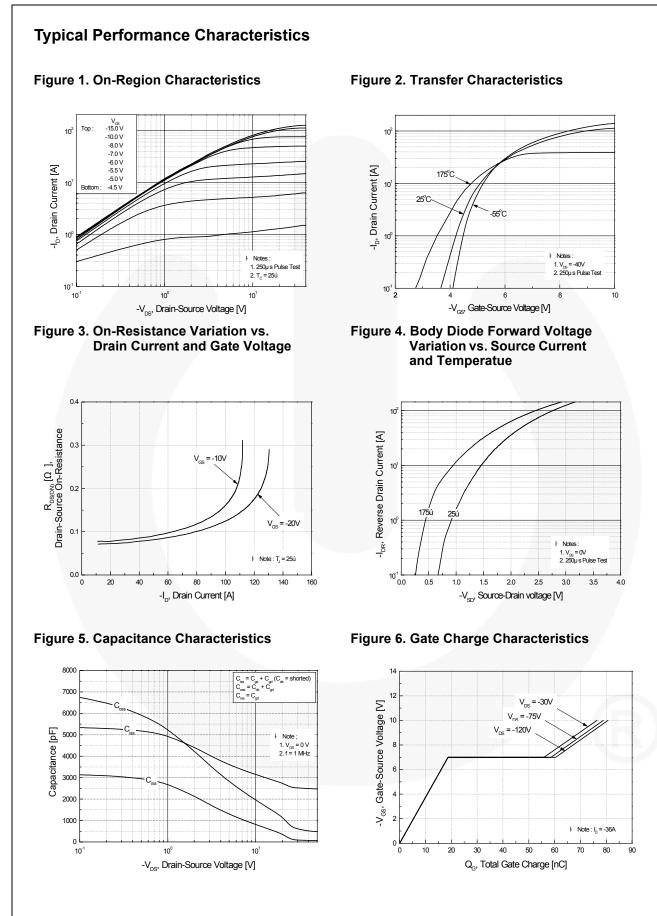
#### Notes:

1. Repetitive rating: pulse-width limited by maximum junction temperature.

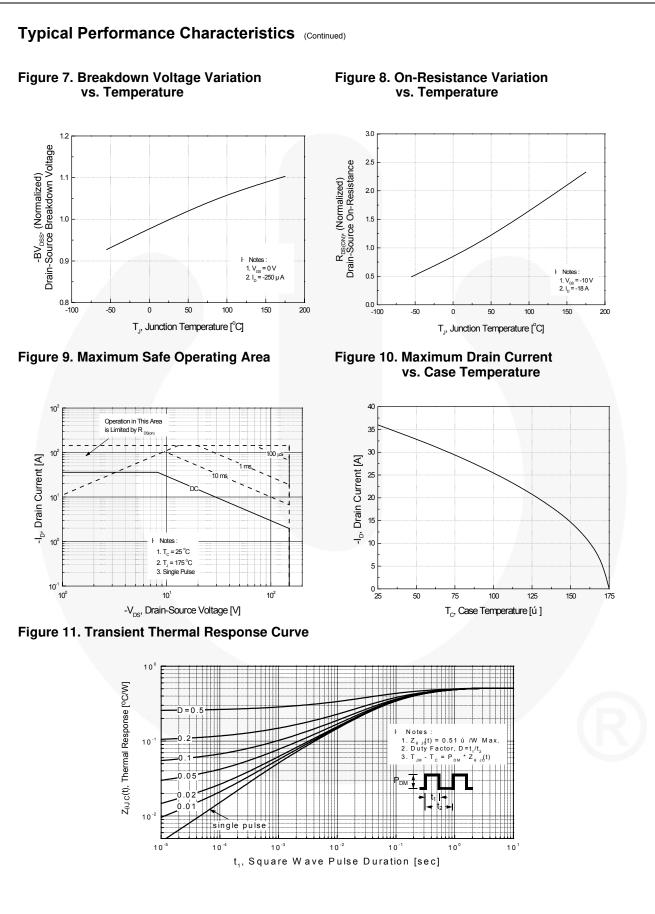
2. L = 1.45 mH, I\_{AS} = -36 A, V\_{DD} = -50 V, R\_G = 25  $\Omega,$  starting T\_J = 25°C.

3.  $I_{SD} \le$  -36 A, di/dt  $\le$  300 A/µs,  $V_{DD} \le$  BV<sub>DSS</sub>, starting T<sub>J</sub> = 25°C.

4. Essentially independent of operating temperature typical characteristics.

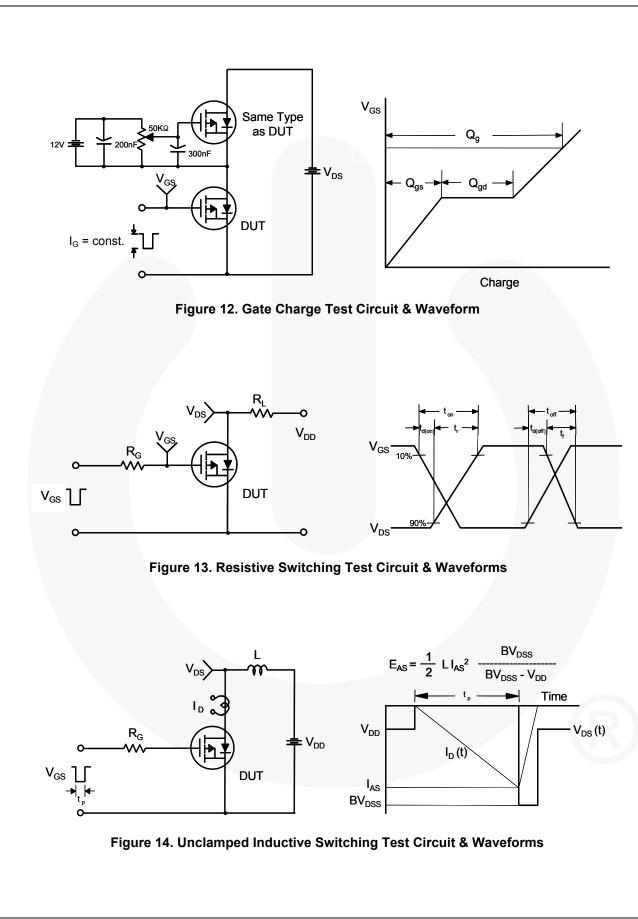


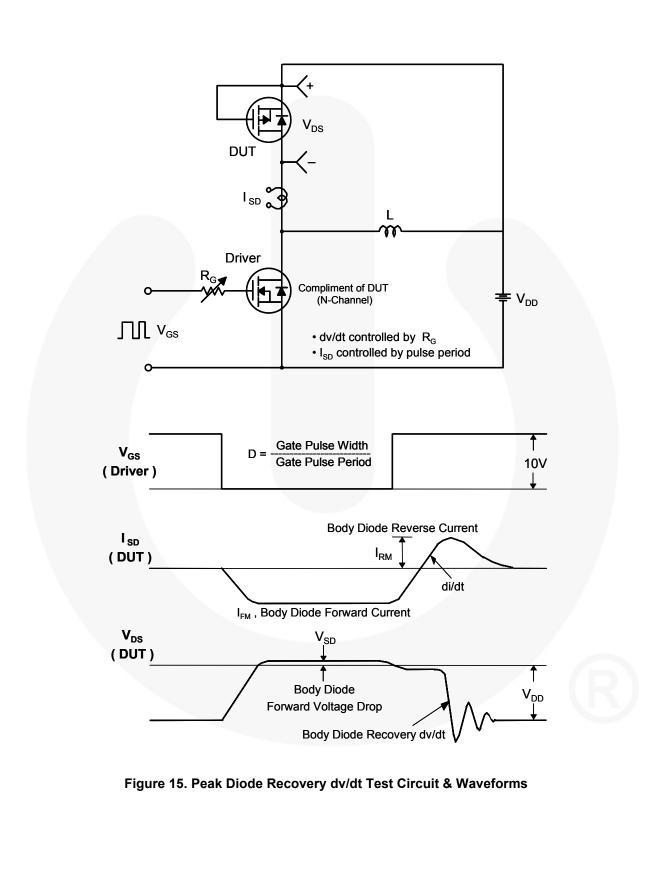
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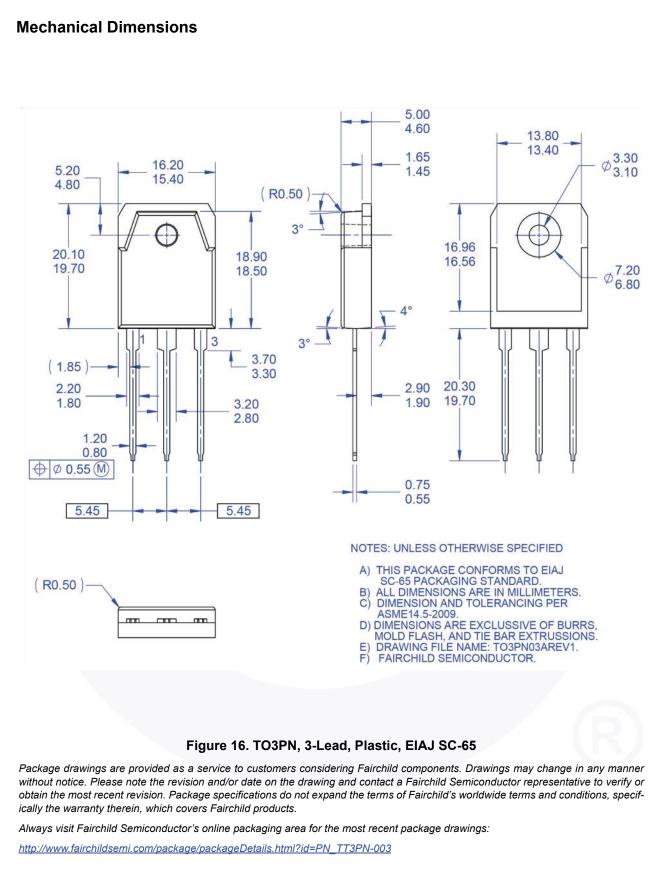


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FQA36P15 — N-Channel QFET<sup>®</sup> MOSFET









 Obsolete
 Not In Production
 Datasheet contains specifications on a product that is discontinued by Fairchild Semiconductor. The datasheet is for reference information only.

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